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FDS6670A

Single N-Channel, Logic Level, PowerTrench^o MOSFET

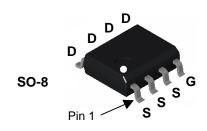
General Description

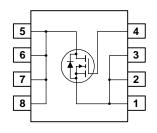
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 13 A, 30 V. $R_{DS(ON)} = 8 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$ $R_{DS(ON)} = 10 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- · Fast switching speed
- · Low gate charge
- High performance trench technology for extremely low R_{DS(ON)}
- High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

| | <u> </u> | | | | |
|-----------------------------------|--|-----------|-------------|-------|--|
| Symbol | Parameter | | Ratings | Units | |
| V _{DSS} | Drain-Source Voltage | | 30 | V | |
| V _{GSS} | Gate-Source Voltage | | ±20 | V | |
| I _D | Drain Current - Continuous | (Note 1a) | 13 | A | |
| | - Pulsed | | 50 | | |
| P _D | Power Dissipation for Single Operation | (Note 1a) | 2.5 | W | |
| | | (Note 1b) | 1.0 | | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | | -55 to +150 | °C | |
| | | | | | |

Thermal Characteristics

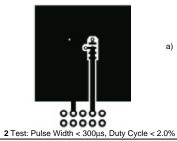
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 50 | °C/W |
|-----------------|---|-----------|-----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1b) | 125 | |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | (Note 1) | 25 | |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity | |
|----------------|-----------------------|-----------|------------|------------|--|
| FDS6670A | FDS6670A FDS6670A 13" | | 12mm | 2500 units | |

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|--|---|---|-----|-----------------|---------------|-------|
| Off Char | acteristics | | | | I. | u e |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$ | 30 | | | V |
| $\Delta BV_{DSS} \over \Delta T_{J}$ | Breakdown Voltage Temperature Coefficient | I_D = 250 μ A, Referenced to 25°C | | 26 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$ | | | 1 | μА |
| | | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | 10 | μА |
| I _{GSS} | Gate-Body Leakage | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | ±100 | nA |
| On Chara | acteristics (Note 2) | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 1 | 1.8 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250 \mu A$, Referenced to $25^{\circ}C$ | | -5.3 | | mV/°C |
| R _{DS(on)} | Static Drain–Source On–Resistance | $V_{GS} = 10 \text{ V}, \qquad I_D = 13 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \qquad I_D = 10.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}, T_J = 125^{\circ}\text{C}$ | | 6 7.2 8.5 | 8 10 14 | mΩ |
| I _{D(on)} | On-State Drain Current | $V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$ | 50 | | | Α |
| g FS | Forward Transconductance | $V_{DS} = 15 \text{ V}, \qquad I_{D} = 13 \text{ A}$ | | 55 | | S |
| Dynamic | Characteristics | | | | | |
| C _{iss} | Input Capacitance | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ | | 2220 | | pF |
| C _{oss} | Output Capacitance | f = 1.0 MHz | | 535 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 200 | | pF |
| R _G | Gate Resistance | V _{GS} = 15 mV, f = 1.0 MHz | | 1.7 | | Ω |
| Switchin | g Characteristics (Note 2) | | | | | |
| t _{d(on)} | Turn-On Delay Time | $V_{DD} = 10 \text{ V}, \qquad I_D = 1 \text{ A},$ | | 11 | 19 | ns |
| t _r | Turn-On Rise Time | $V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$ | | 13 | 24 | ns |
| t _{d(off)} | Turn-Off Delay Time | | | 40 | 64 | ns |
| t _f | Turn-Off Fall Time | | | 13 | 24 | ns |
| Qg | Total Gate Charge | $V_{DS} = 15 \text{ V}, \qquad I_{D} = 13 \text{ A},$ | | 21 | 30 | nC |
| Q _{gs} | Gate-Source Charge | $V_{GS} = 5 V$ | | 6 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 7 | | nC |
| Drain-So | ource Diode Characteristics | and Maximum Ratings | | | | |
| Is | Maximum Continuous Drain-Source | | | | 2.1 | Α |
| V_{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, \qquad I_{S} = 2.1 \text{ A (Note 2)}$ | | 0.7 | 1.2 | V |
| t _{rr} | Diode Reverse Recovery Time | 1 - 13 A d /d - 100 A/vo | | 31 | | nS |
| Q _{rr} | Diode Reverse Recovery Charge | $I_F = 13 \text{ A}, 	 d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$ | | 21 | | nC |

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 125°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

Typical Characteristics

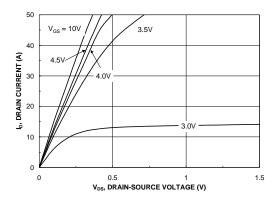


Figure 1. On-Region Characteristics.

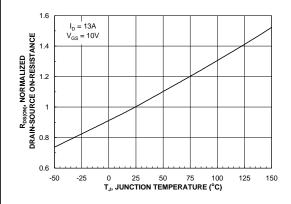


Figure 3. On-Resistance Variation with Temperature.

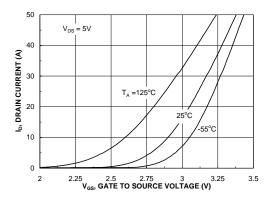


Figure 5. Transfer Characteristics.

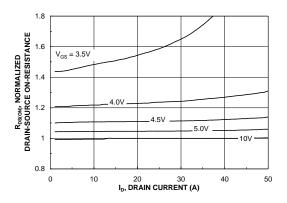


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

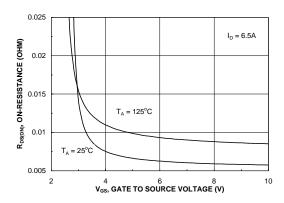


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

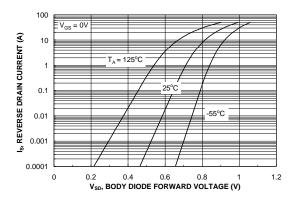
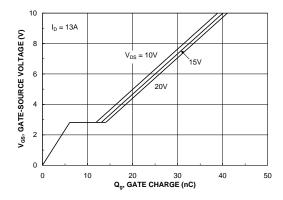


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



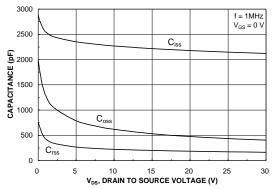
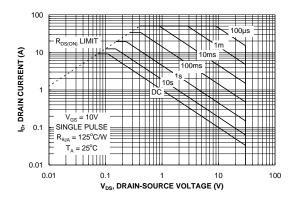


Figure 7. Gate Charge Characteristics.





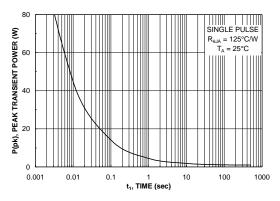


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

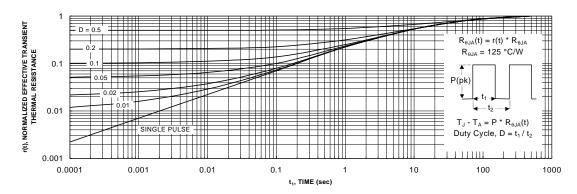


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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